

MAINTENANCE MANUAL

66-88 MHz POWER AMPLIFIER ASSEMBLY 19D424673GI

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DESCRIPTION

The 66-88 MHz PA assembly for MASTR® Executive II uses two RF power transistors to provide a power output of 25 watts. The output power is adjustable using power adjust control R3 over a range of 8 to 25 watts. A single transistor is used in the power adjust circuit.

Supply voltage for the PA is connected through power leads from the system-audio-squelch board (SAS) to feed through capacitors C297 and C298 on the side of the PA assembly. C297, C298 and C299 prevent RF from getting on the power leads. Diode CR295 will cause the main fuse assembly to blow if the polarity of the power leads is reversed, providing reverse voltage protection for the radio.

The PA assembly is insulated from vehicle ground to permit operation in positive or negative ground vehicles.

- NOTE -

In positive ground vehicles, Ais "hot" with respect to vehicle
ground. Shorting the transmitter
PA printed wiring board ground
pattern to the radio case may
cause one of the in-line fuses to
blow.

The hinged PA heat sink pivots 90° to provide access to the power amplifier board, low pass filter and centralized metering jack J205.

Centralized metering jack J205 is provided for use with GE Test Set Model 4EX3All or Test Kit 4EX8Kl2. The Test Set meters the Ampl-1 drive (exciter output), power control voltage (Ampl-1 collector voltage) and PA current.

CIRCUIT ANALYSIS

RF AMPLIFIERS

The exciter output is coupled through cable W216 to PA input jack J201. The RF is coupled through DC blocking capacitor C1 and an impedance matching network to the base of Class C amplifier Q201. The network matches the 50-ohm input to the base of Q201, and consists of C2, C3, C4, L1 and L2. L3 and R1 comprise a stabilizing network in the base circuit of Q201.

Part of the RF input is rectified by CR1 and applied to voltage divider R7 and R8. This voltage is used to meter the AMPL-1 drive at J205-4.

Collector voltage to Q201 (Ampl-1) is controlled by the power adjust circuit, Q215 and R3 and is applied through collector stabilizing network (L5 and R2 and collector feed network L4 and C7). The collector voltage of Q201 is metered through R9 at J205-3.

The output of Q201 is coupled to the base of Class C Power Amplifier, Q202, through coupling capacitor C10 and a matching network consisting of L6, C11, C12, and C13. L8 and R4 comprise a stabilizing network in the base circuit of Q202.

Collector current for Q202 is metered across tapped manganin resistor R6 at J205-5, 6 (PA Current). The reading is taken on the one-Volt scale with the High Sensitivity button pressed, and read as 10 amperes full scale.

Following Q202 is a matching network (L11, C17, C18 and L12) that matches the output of Q202 to the 50-ohm microstrip impedance (W2) to the input of low pass filter.

The PA output is coupled through the low-pass filter antenna transfer relay K1 to the antenna.

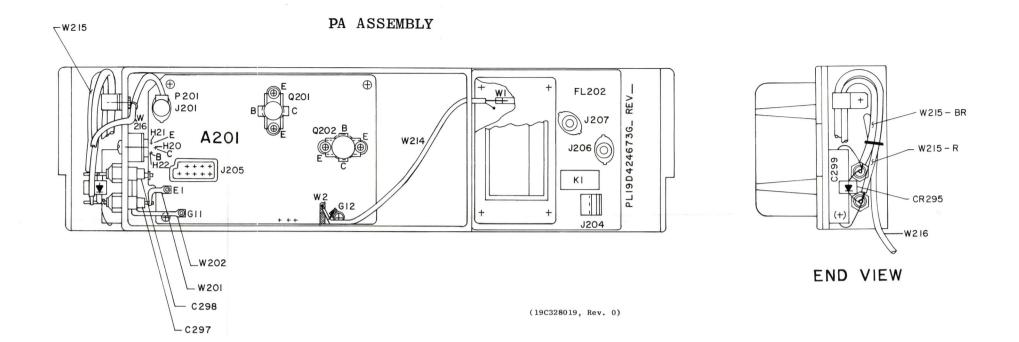
Capacitor C19 through C23 and C25, C26 and C36 provide ground isolation for positive and negative ground operation.

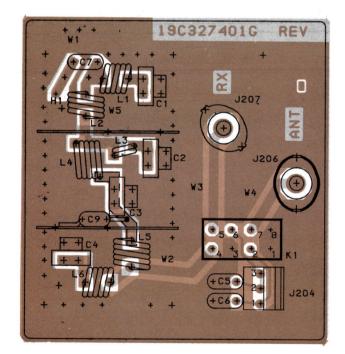
- WARNING -

The RF Power Transistors used in the transmitter contain Beryllium Oxide, a TOXIC substance. If the ceramic, or other encapsulation is opened, crushed, broken or abraded, the dust may be hazardous if inhaled. Use care in replacing transistors.

POWER ADJUST CIRCUIT

The power adjust circuit consists of R3 and Q215. R3 controls the base voltage and therefore the conduction of Q215. Q215 is connected in series with the collector feed network for Q201 thereby controlling the drive to PA transistor Q202 and the output power. R3 is adjusted to provide the desired output power over a range of 8 to 25 watts.





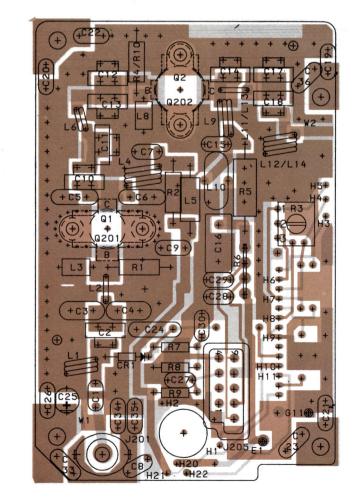
(19C327850, Rev. 2) (19B227594, Sh. 1, Rev. 0) (19B227594, Sh. 2, Rev. 0)

OUTLINE DIAGRAM

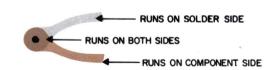
66-88 MHz POWER AMPLIFIER

Issue 2

LOW PASS FILTER FL201

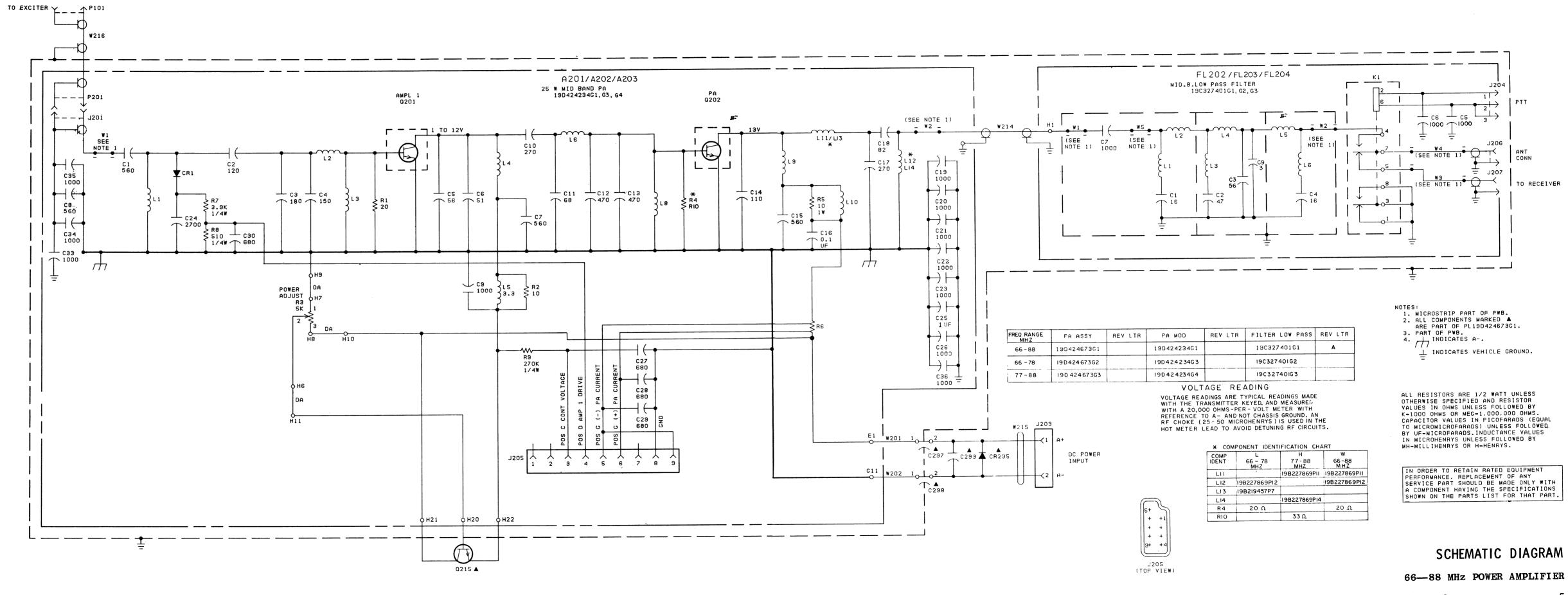


PA BOARD A201



CONNECTION CHART				
FROM	TO	WIRE	REMARKS	
H10	H8	DA	SLEEVE	
H11	Н6	DA	SLEEVE	
H7	Н9	DA	SLEEVE	

TO RECEIVER



LBI30553

PARTS LIST

LBI30558A

66-88 MHz 25 WATT POWER AMPLIFIER

66-88 MHZ 25 WATT POWER AMPLIFIER 19D424673G1 66-88 MHZ 19D424673G2 66-78 MHZ			LS	7488079P10	Choke, RF: 3.30 µh ±10%, 0.1 sim to Jeffers 4421-1K.
		19D424673G3 77-89 MHz	L6	19B227869P9	Coil.
			L8	19A129773G1	Coil.
0.44501	05 0407 110		L9	19B227869P10	Coil.
SYMBOL	GE PART NO.	DESCRIPTION	L10	19A129346G1	Coil.
			L11	19B227869P11	Coil.
A201 thru		25 WATT MODULE	L12	19B227869P12	Coil,
A203		A201 19D424234G1 66-88 MHz A202 19D424234G3 66-78 MHz	L13	19B219457P7	Coil.
		A203 19D424234G4 77-89 MHz	L14	19B227869P14	Coil.
		CAPACITORS			RESISTORS
C1	19A116655P15	Ceramic disc: 560 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	R1	3R77P200J	Composition: 20 ohms ±5%, 1/
C2	19A116679P120J	Silver mica: 120 pf ±5%, 250 VDCW.	R2	3R77P100J	Composition: 10 ohms ±5%, 1/
С3	7489162P33	Silver mica: 180 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	R3	19A116559P102	Variable, cermet: 5K ohms ±20 CTS Series 360.
C4	7489162P31	Silver mica: 150 pf ±5%, 500 VDCW; sim to Electro Motive Type DM-15.	R4	3R77P200J	Composition: 20 ohms ±5%, 1/3
C5	19A116656P56J8	Ceramic disc: 56 pf ±5%, 500 VDCW, temp coef	R5 R6	3R78P100J 19C320212P2	Composition: 10 ohms ±5%, 1
C6	19A116656P51J8	-80 PPM. Ceramic disc: 51 pf ±5%, 500 VDCW, temp coef	R7	3R152P392J	Shunt resistor. omposition: 3.9K ohms ±5%, 1,
	10,110,000,010	-80 PPM.	R8	3R152P511J	Composition: 510 ohms ±5%, 1
C7 and C8	19A116655P15	Ceramic disc: 560 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	R9	3R152P274J	Composition: 270K ohms ±5%, 1
C9	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.			
C10	19Al16679P270J	Mica: 270 pf ±5%, 250 VDCW.	Wl and		(Part of 19D424233Pl printed b
C11	19A116679P68J	Mica: 68 pf ±5%, 250 VDCW.	W2		
C12	19A116679P470J	Mica: 470 pf ±5%, 250 VDCW.	0007	1041167007	
and C13			C297 and C298	19A116708P1	Ceramic, feed-thru: 0.01 µf sim to Erie Style 327.
C14	19A116679P110J	Mica: 110 pf ±5%, 250 VDCW.	C299	19A115680P10	Electrolytic: 200 μf +150% -1
C15	19A116655P15	Ceramic disc: 560 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.		15411000710	to Mallory Type TTX.
C16	19A116966P107	Metallized polyester: 0.1 μf ±10%, 50 VDCW.			DIODES AND REC
C17	19A116679P270J	Mica: 270 pf ±5%, 250 VDCW.	CR295	19A116783P1	Silicon.
C18	19A116679P82J	Mica: 82 pf ±5%, 250 VDCW.		1	FILTERS
C19 thru C23	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	FL202		COMPONENT BOA
C24	19A116655P21	Ceramic disc: 2700 pf ±20%, 1000 VDCW; sim to RMC Type JF Discap.	fL204		19C327401G1 66-8 19C327401G2 66-7 19C327401G3 77-8
C25	19A134202P14	Tantalum: 1 μf ±20%, 35 VDCW.			CADACITORS
C26	19A116655P20	ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.	C1	19A16679P16D	
C27	19A116655P18	Ceramic disc: 680 pf ±10%, 1000 VDCW; sim	C2	19A116679P47J	Metallized teflon: 47 pf ±5%,
thru C30		to RMC Type JF Discap.	СЗ	19A16679P56J	Silver mica: 56 pf ±5%, 250 v
C33	19A116655P20	Ceramic disc: 1090 pf ±10%, 1000 VDCW; sim	C4	19A16679P16D	Metallized teflon: 16 pf ±.5
thru C36		to RMC Type JF Discap.	C5 thru	19A116655P20	Ceramic disc: 1000 pf ±10%, 1
		DIODES AND RECTIFIERS	C8		RMC Type JF Discap.
CR1	19A115250P1	Silicon, fast recovery, 225 mA, 50 PIV.	C9*	19A116656P3J0	Ceramic disc: 3 pf ±0.5 pf, 5 0 PPM. Added to G1 by REV A.
El	19A134263P1	Contact, electrical: sim to Selectro 22901082- 00-0-590.	J 204	19A116659P55	Connector, printed wiring: 3 Molex 09-52-65-1031,
G11	19A134263PJ	Contact, electrical: sim to Selectro 229-1082- 00-0-590.	J206 and	19A130924G1	Connector, receptacle: coaxia sim to Cinch 14H116113.
			J207		
J2 01	19A130924G1	Receptacle, coaxial: jack type; sim to Cinch			RELAYS -
J 205	19B219374G1	14H11613. Connector: 9 contacts.	K1	19B209558Pl	Hermetic sealed: 180 to 341 o 2 form C contacts, 8.0 to 16.3 3SAV1760A2.
Ll	19B227869P6	Coil.		10-00-06	INDUCTORS
L2	19B227869P7	Co11.	Ll	19B227869P1	Coil.
L3	19A129773G1	Coil.	L2	19B227869P2	Coil.
			L3	19B227869P3	Coil.

SYMBOL	GE PART NO.	DESCRIPTION	SYMBOL	GE PART NO.	DESCRIPTION
L4	19B227869P8	Coil.	L4	19B227869P4	Coil.
L5	7488079P10	Choke, RF: 3.30 µh ±10%, 0.15 ohms DC res max;	L5	19B227869P5	Coil.
		sim to Jeffers 4421-1K.	L6	19B227869P13	Coil.
L6	19B227869P9	Coil.			
L8	19A129773G1	Coil,			
L9	19B227869P10	Coil,	W1 thru		(Part of printed board 19C327400P1).
L10	19A129346G1	Coil.	W5		
Lll	19B227869P11	Coil.			
L12	19B227869P12	Coil.	Q201	19A134489P1	Silicon, NPN.
L13	19B219457P7	Coil.	Q202	19A134489P2	Silicon, NPN.
L14	19B227869P14	Coil.	Q215	19A116742P1	Silicon, NPN.
		RESISTORS			77.17.0
Rl	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.	P201		
R2	3R77P100J	Composition: 10 ohms ±5%, 1/2 w.	P203		(Part of W215).
R3	19A116559P102	Variable, cermet: 5K ohms ±20%, .5 w; sim to CTS Series 360.	1200		
R4	3R77P200J	Composition: 20 ohms ±5%, 1/2 w.	W201	10000700401	
R5	3R78P100J	Composition: 10 ohms ±5%, 1 w.	W201	19B227024P1 19B227025G1	Jumper.
R6	19C320212P2	Shunt resistor.	W202 W214		Jumper,
R7	3R152P392J	omposition: 3.9K ohms ±5%, 1/4 w.	W214	19A130831G2	Cable, RF: approx 5-1/4 inches long.
R8	3R152P511J	Composition: 510 ohms ±5%, 1/4 w.	W215		CABLE ASSEMBLY
R9	3R152P274J	Composition: 270K ohms ±5%, 1/4 w.			19B227058G1
W1		(Part of 19D424233Pl printed board).	J203		Connector. Includes:
and W2		,		19A134281P2	Shell.
				19A134282P4	Contact, electrical. (Quantity 2).
C297	19A116708P1	Ceramic, feed-thru: 0.01 µf +100% -0%, 500 VDCW; sim to Erie Style 327.	1		MISCELLANEOUS
298		3 3. 2 3.,10 32	-	7117269P1	Solderless terminal.
C299	19A115680P10	Electrolytic: 200 µf +150% -10%, 18 VDCW; sim to Mallory Type TTX.	W216	19A130909G1	Cable, RF: approx 7-1/2 inches long. Includes P201 (5491689P91).
		DIODES AND RECTIFIERS			MISCELLANEOUS
CR295	19A116783P1	Silicon,		19C321591G4	Casting, heat sink.
				19C321441P2	Insulator. (Located between A201 and heat sink).
				N44P9006C6	Machine screw: No. 4-40 x 3/8. (Secures Q201,
L202 thru		COMPONENT BOARD 19C327401G1 66-88 MHz		10410056071	(202).
FL204		19C327401G2 66-78 MHz 19C327401G3 77-89 MHz		19A130568P1 19A116023P1	Plate. (Located under Q215 next to heat sink). Insulator, plate. (Used with Q215 next to
				19A134016P1	19A130568Pl plate). Insulator, bushing. (Located under 4-40 nut at
C1	19A16679P16D	Metallized teflon: 16 pf ±.5 pf 250 VDCW.	1		Q215).
C2	19A116679P47J	Metallized teflon: 47 pf ±5%, 250 VDCW.	İ	19A129434P1	Washer, fiber. (Used with C297, C298).
C3	19A16679P56J	Silver mica: 56 pf ±5%, 250 VDCW.	-	19B201074P305	Tap screw, Phillips POZIDRIV®: No. 6-32 x 5/16. (Secures A201- Quantity 3).
C4	19A16679P16D	Metallized teflon: 16 pf ±.5 pf, 250 VDCW.	1	19B201074P306	Tap screw, Phillips POZIDRIVe: No. 6-32 x 3/8.
C5 thru C8	19A116655P20	Ceramic disc: 1000 pf ±10%, 1000 VDCW; sim to RMC Type JF Discap.		7878455P2	(Secures A201 and solderless terminal 7878455P2- Quantity 3). Solderless terminal. (Located on A201 mounting
C9*	19A116656P3J0	Ceramic disc: 3 pf ±0.5 pf, 500 VDCW, temp coef 0 PPM. Added to G1 by REV A.		4029851P6	screw). Clip loop. (Secures W215).
				19C321982P1	Insulator. (Located under A201-A203).
J204	19A116659P55	Connector, printed wiring: 3 contacts; sim to	İ	19B201074P320	Tap screw, Phillips POZIDRIV®: No. 6-32 x 1-1/4.
		Molex 09-52-65-1031.	i	7139898 P 3	(Secures FL202-FL204).
J206 and J207	19A130924G1	Connector, receptacle: coaxial, jack type; sim to Cinch 14H116113.		7139090P3	Hex nut: brass, (Used with C297 and C298).
	l				
K1	19B209558Pl	Hermetic sealed: 180 to 341 ohms coil res, 2 form C contacts, 8.0 to 16.3 VDC; sim to GE 3SAV1760A2.			
		INDUCTORS			
L1	19B227869Pl	Coil.	1 1		

*COMPONENTS ADDED, DELETED OR CHANGED BY PRODUCTION CHANGES

PRODUCTION CHANGES

Changes in the equipment to improve performance or to simplify circuits are identified by a "Revision Letter", which is stamped after the model number of the unit. The revision stamped on the unit includes all previous revisions. Refer to the Parts List for descriptions of parts affected by these revisions.

- See - F

Low Pass Filter Assembly 19C327401G1

REV. A - To improve operation. Added C9.